

Myung-Geun Han

List of Publications by Year in descending order

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35
papers

1,345
citations

430874

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454955

30
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all docs

35
docs citations

35
times ranked

2874
citing authors

#	ARTICLE	IF	CITATIONS
1	Polaronic Conductivity in Cr ₂ Ge ₂ Te ₆ Single Crystals. <i>Advanced Functional Materials</i> , 2022, 32, .	14.9	7
2	Electrostatic Asymmetry of Wurtzite Nanocrystals and Resulting Photocatalytic Properties. <i>Journal of Physical Chemistry C</i> , 2022, 126, 4751-4761.	3.1	0
3	<i>Operando</i> characterization of conductive filaments during resistive switching in Mott VO ₂ . <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2021, 118, .	7.1	15
4	In situ cryo-electron microscopy of two-dimensional van der Waals magnets. <i>Microscopy and Microanalysis</i> , 2021, 27, 326-328.	0.4	0
5	Antiphase-Boundary-Engineered Domain Switching in a (110)-Oriented BiFeO ₃ Film. <i>ACS Applied Electronic Materials</i> , 2021, 3, 3226-3233.	4.3	4
6	Hybrid Symmetry Epitaxy of the Superconducting Fe(Te,Se) Film on a Topological Insulator. <i>Nano Letters</i> , 2021, 21, 6518-6524.	9.1	9
7	Homochiral Skyrmionic Bubbles in Exfoliated 2D Van Der Waals Cr ₂ Ge ₂ Te ₆ . <i>Microscopy and Microanalysis</i> , 2020, 26, 2138-2140.	0.4	0
8	Quantum Hall to Insulator Transition in Ultra-Low Carrier Density Topological Insulator Films and a Hidden Phase of the Zeroth Landau Level. <i>Advanced Materials</i> , 2019, 31, e1901091.	21.0	19
9	Deterministic Ferroelastic Domain Switching Using Ferroelectric Bilayers. <i>Nano Letters</i> , 2019, 19, 5319-5326.	9.1	15
10	The in situ Studies on the Anomalous Domain Switching Caused by Trace Amount of Oxygen Vacancies. <i>Microscopy and Microanalysis</i> , 2019, 25, 1888-1889.	0.4	0
11	Topological Magnetic-Spin Textures in Two-Dimensional van der Waals Cr ₂ Ge ₂ Te ₆ . <i>Nano Letters</i> , 2019, 19, 7859-7865.	9.1	116
12	Engineering Topological Superlattices and Phase Diagrams. <i>Nano Letters</i> , 2019, 19, 716-721.	9.1	5
13	Revealing the Effects of Trace Oxygen Vacancies on Improper Ferroelectric Manganite with In Situ Biasing. <i>Advanced Electronic Materials</i> , 2019, 5, 1800827.	5.1	8
14	Record High-Proximity-Induced Anomalous Hall Effect in (Bi _x Sb _{1-x}) ₂ Te ₃ Thin Film Grown on CrGeTe ₃ Substrate. <i>Nano Letters</i> , 2019, 19, 4567-4573.	9.1	34
15	Dipole-like electrostatic asymmetry of gold nanorods. <i>Science Advances</i> , 2018, 4, e1700682.	10.3	39
16	Interface reconstruction with emerging charge ordering in hexagonal manganite. <i>Science Advances</i> , 2018, 4, eaar4298.	10.3	37
17	Atomically Thin CBRAM Enabled by 2-D Materials: Scaling Behaviors and Performance Limits. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4160-4166.	3.0	19
18	Linearly aligned single-chiral vortices in hexagonal manganites by electric arc heating. <i>Physical Review Materials</i> , 2018, 2, .	2.4	4

#	ARTICLE	IF	CITATIONS
19	Publisher's note. Ultramicroscopy, 2017, 177, 14-19.	1.9	5
20	Optical Asymmetry and Nonlinear Light Scattering from Colloidal Gold Nanorods. ACS Nano, 2017, 11, 5925-5932.	14.6	23
21	Electron-beam-induced-current and active secondary-electron voltage-contrast with aberration-corrected electron probes. Ultramicroscopy, 2017, 176, 80-85.	1.9	14
22	Atomically Thin Femtojoule Memristive Device. Advanced Materials, 2017, 29, 1703232.	21.0	147
23	Electrostatic Potential Mapping by Secondary-electron Voltage-contrast and Electron-beam-induced-current in TEM. Microscopy and Microanalysis, 2017, 23, 1424-1425.	0.4	0
24	Topologically Allowed Nonsixfold Vortices in a Sixfold Multiferroic Material: Observation and Classification. Physical Review Letters, 2017, 118, 145501.	7.8	20
25	Record Surface State Mobility and Quantum Hall Effect in Topological Insulator Thin Films via Interface Engineering. Nano Letters, 2015, 15, 8245-8249.	9.1	119
26	Robust topological surface states of Bi ₂ Se ₃ thin films on amorphous SiO ₂ /Si substrate and a large ambipolar gating effect. Applied Physics Letters, 2014, 104, .	3.3	28
27	Observation of Ferroelectricity and Structure-Dependent Magnetic Behavior in Novel One-Dimensional Motifs of Pure, Crystalline Yttrium Manganese Oxides. Journal of Physical Chemistry C, 2014, 118, 21695-21705.	3.1	11
28	Interface-induced nonswitchable domains in ferroelectric thin films. Nature Communications, 2014, 5, 4693.	12.8	120
29	Ferroelectric Switching Dynamics of Topological Vortex Domains in a Hexagonal Manganite. Advanced Materials, 2013, 25, 2415-2421.	21.0	91
30	Ferroelectric order in individual nanometre-scale crystals. Nature Materials, 2012, 11, 700-709.	27.5	292
31	Origin of 90° domain wall pinning in Pb(Zr _{0.2} Ti _{0.8})O ₃ heteroepitaxial thin films. Applied Physics Letters, 2011, 99, 102902.	3.3	49
32	Quantitative phase imaging of nanoscale electrostatic and magnetic fields using off-axis electron holography. Ultramicroscopy, 2010, 110, 375-382.	1.9	45
33	<i>In situ</i> electron holographic analysis of biased Si n+p junctions. Applied Physics Letters, 2008, 92, .	3.3	13
34	Quantitative Analysis of 2-D Electrostatic Potential Distributions in 90-nm Si pMOSFETs Using Off-Axis Electron Holography. IEEE Transactions on Electron Devices, 2007, 54, 3336-3341.	3.0	19
35	Sample Preparation for Precise and Quantitative Electron Holographic Analysis of Semiconductor Devices. Microscopy and Microanalysis, 2006, 12, 295-301.	0.4	18